Method and device for producing monocrystals

Abstract

The invention relates to a method for producing a silicon monocrystal, in which the growing monocrystal is kept for a specified dwell time in a specified temperature range, wherein the range from 850 to 1100°C is chosen as the temperature range and the dwell time of the growing monocrystal in the chosen temperature range is either greater than 250 min or less than 80 min. The invention also relates to a device and a method, in which the cooling rate of the growing monocrystal is influenced by a heat shield which is subdivided into annular zones between a lower rim and an upper rim, adjacent zones differing in regard to thermal conduction and transparency to heat radiation.

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